Product data sheet

1. General description

AC Thyristor Triac power switch in a SOT404 (D2PAK) surface mountable plastic package with self-protective clamping capabilities against low and high energy transients. This "series CT" triac will commutate the full RMS current at the maximum rated junction temperature ($T_{j(max)}$ = 150 °C) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- High junction operating temperature capability
- Full cycle AC conduction
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Protective self turn-on capability for high energy transients
- Safe clamping capability for low energy over-voltage transients
- Less sensitive gate for high noise immunity
- Surface mountable package
- Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls
- Applications subject to high temperature

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5	-	-	120	Α
Tj	junction temperature		_	-	150	°C





Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 120 °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	12	Α
V_{PP}	peak pulse voltage	T _j = 25 °C; non-repetitive, off-state; Fig. 6	-	-	2	kV
Static charac	teristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; LD+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	35	mA
		$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; LD+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	35	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD- G-;}$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	35	mA
V _{CL}	clamping voltage	I_{CL} = 0.1 mA; t_p = 1 ms; T_j = 25 °C	850	-	-	V
Dynamic cha	racteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	500	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	5	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Table 2.	ı ııııııı	IIIIOIIIIatioii		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	СМ	common	mb	LD I
2	LD	load		G
3	G	gate		CM
mb	LD	mounting base; load	D2PAK (SOT404)	003aaf296
			D2PAR (501404)	

6. Ordering information

Table 3. Ordering information

Type number		Package		
		Name	Description	Version
	ACTT12B-800CT	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

ACTT12B-800CT

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7. Marking

Table 4. Marking codes

Type number	Marking code
ACTT12B-800CT	ACTT12B-800CT

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 120 \text{ °C}$; Fig. 1; Fig. 2; Fig. 3	-	12	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	120	A
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 16.7 ms$	-	132	A
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	72	A ² s
dl _T /dt	rate of rise of on-state current	I_T = 12 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s	-	100	A/µs
I _{GM}	peak gate current	t = 20 μs	-	2	Α
P_{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	150	°C
V_{PP}	peak pulse voltage	T _j = 25 °C; non-repetitive, off-state; Fig. 6	-	2	kV

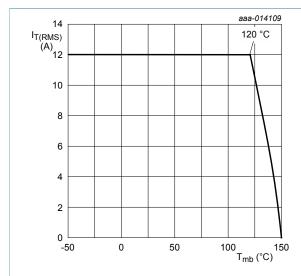


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

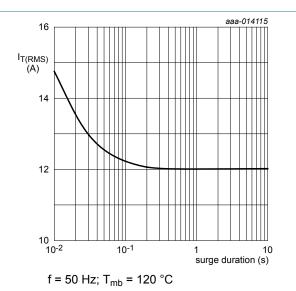


Fig. 2. RMS on-state current as a function of surge duration; maximum values

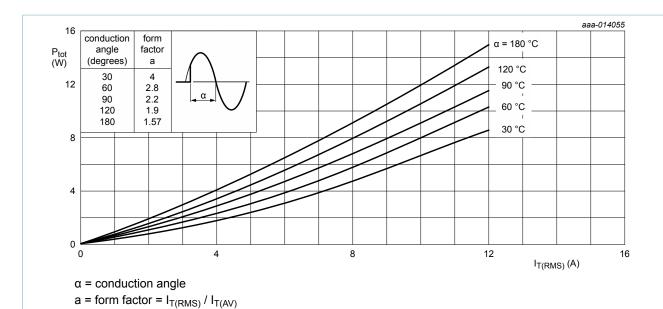


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

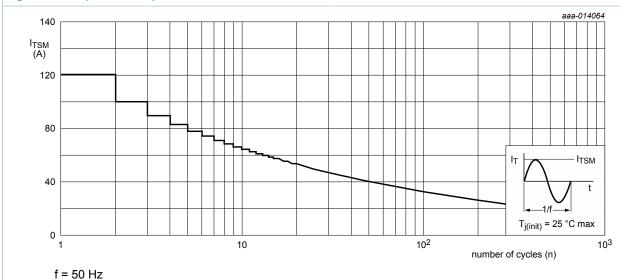


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

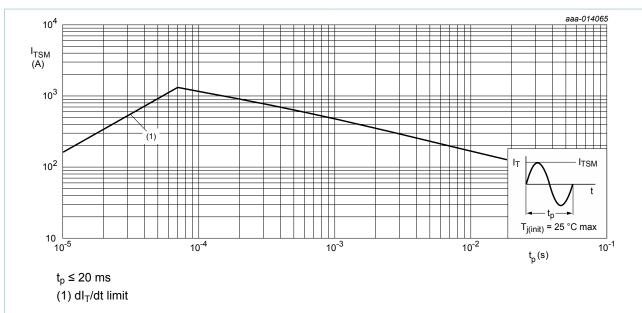


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

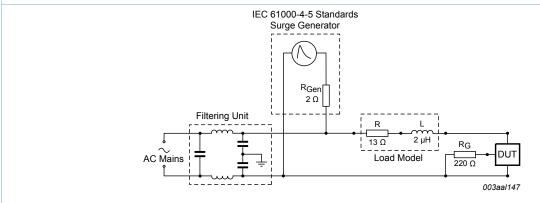


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	full cycle; Fig. 7	-	-	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air; printed circuit board (FR4) mounted	-	60	-	K/W

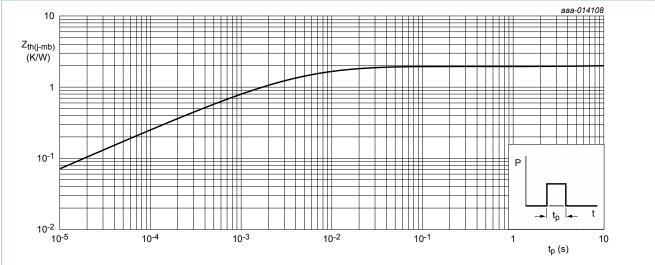


Fig. 7. Transient thermal impedance from junction to mounting base as a function of pulse width

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		,			
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G+;}$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	35	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	35	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD- G-;}$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	35	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 100 \text{ mA}; LD+ G+;$ $T_j = 25 \text{ °C}; Fig. 9$	-	-	50	mA
		$V_D = 12 \text{ V; } I_G = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; } Fig. 9$	-	-	70	mA
		$V_D = 12 \text{ V; } I_G = 100 \text{ mA; LD- G-;}$ $T_j = 25 \text{ °C; } \underline{Fig. 9}$	-	-	50	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 10</u>	-	-	50	mA
V _T	on-state voltage	I _T = 17 A; T _j = 25 °C; <u>Fig. 11</u>	-	1.25	1.5	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; T_j = 25 ^{\circ}\text{C};$ Fig. 12	-	0.8	1	V
		$V_D = 400 \text{ V}; I_T = 100 \text{ mA}; T_j = 150 ^{\circ}\text{C};$ Fig. 12	0.2	0.45	-	V
I _D	off-state current	V _D = 800 V; T _j = 25 °C	-	-	10	μΑ
		V _D = 800 V; T _j = 150 °C	-	-	2	mA
V _{CL}	clamping voltage	I_{CL} = 0.1 mA; t_p = 1 ms; T_j = 25 °C	850	-	-	V
Dynamic c	haracteristics		l			
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _j = 150 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	500	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 20 V/µs; (snubberless condition); gate open circuit	5	-	-	A/ms

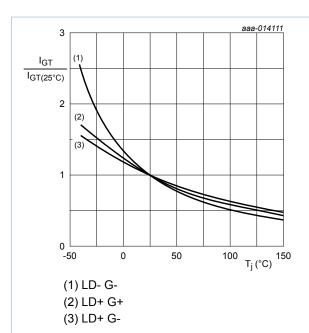


Fig. 8. Normalized gate trigger current as a function of junction temperature

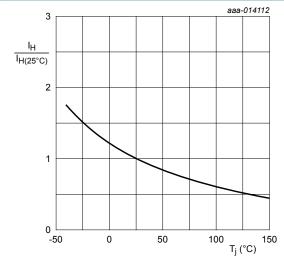


Fig. 10. Normalized holding current as a function of junction temperature

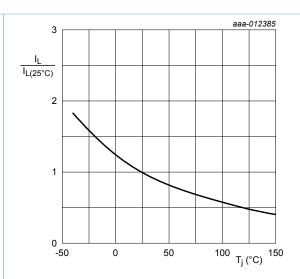
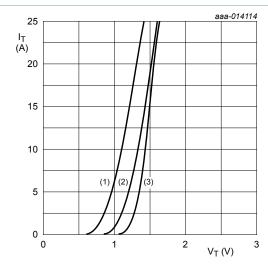


Fig. 9. Normalized latching current as a function of junction temperature



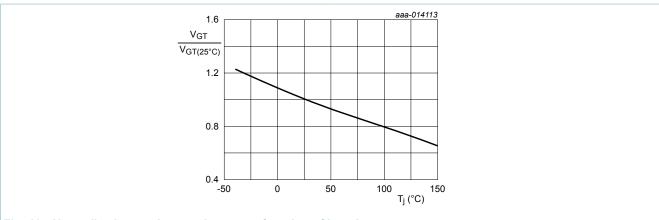
 $V_o = 0.982 \text{ V}; R_s = 0.029 \Omega$

(1) T_i = 150 °C; typical values

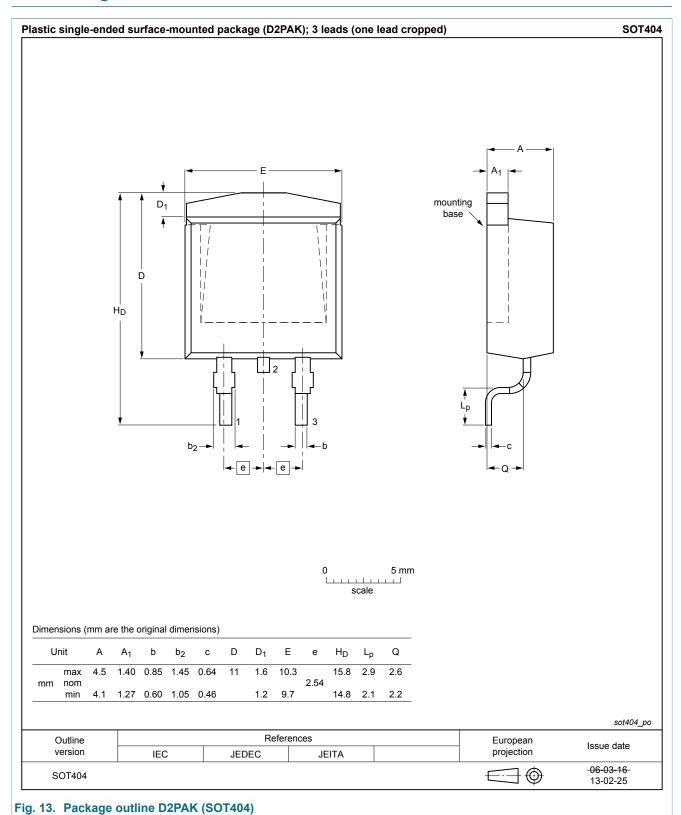
(2) T_i = 150 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 11. On-state current as a function of on-state voltage



11. Package outline



12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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